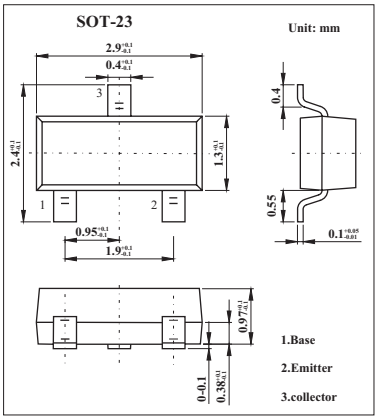
TY Semicondutor®

Product specification

2SA1981SF



■ Features

● High Hfe:.h_{FE}=100 to 320

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-35	V
Collector-emitter voltage	V_{CEO}	-30	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-800	mA
Collector dissipation	P_C	200	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV_{CBO}	I_C=-500μA , I_E=0	-35			V
Collector-emitter breakdown voltage	BV_{CEO}	I_C=-1mA , I_B=0	-30			V
Emitter-base breakdown voltage	BV_{EBO}	I_E=-50μA, I_C=0	-5			V
Collector cutoff current	I_{CBO}	V_{CB}=-35V, I_E=0			-0.1	μA
Emitter cutoff current	I_{EBO}	V_{EB}=-5V, I_C=0			-0.1	μA
DC current transfer ratio	h_{FE}	V_{CE}=-1V, I_C=-100mA	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	Ic/I_B=-500mA/-20mA			-0.5	V
Transition frequency	f_T	V_{CE}=-5V, I_E=10mA,		120		MHz
Output capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz		19		pF

■ h_{FE} Classification

Marking	EA	
Rank	O	Y
hFE	100～200	160～320